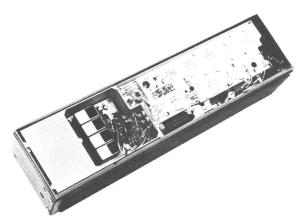


MASTR Progress Line

406-470 MHz, RECEIVER MODELS 4ER42F10-27 & 4ER42H10-27



SPECIFICATIONS*

FCC Filing Designation

Frequency Range

Audio Output

Sensitivity

12-dB SINAD (EIA Method) 20-dB Quieting Method

Intermodulation (EIA)

Selectivity

EIA Two-Signal Method 20-dB Quieting Method

Spurious Response

First Oscillator Stability

Type ER-42-F Receivers Type ER-42-H Receivers

Modulation Acceptance

Squelch Sensitivity

Critical Squelch Standard Receiver UHS Receiver Maximum Squelch

Maximum Frequency Separation

Frequency Response

ER-42-F & H

406-420 & 450-470 MHz

5 watts at less than 5% distortion

Standard Receiver	Ultra-High Sensitivity Receiver
0.35 μV 0.50 μV	0.20 μV 0.25 μV
-75 dB	-70 dB
05 15 ()	

-85 dB (adjacent channel, 50 kHz channels) -100 dB at ± 35 kHz

-100 dB

 $\pm .0005\%$ (-30°C to +60°C) $\pm .0002\%$ (-30°C to +60°C)

 ± 19 kHz

0.2 µV 0.15 μV Greater than 20 dB quieting (less than 1.5 μ V)

0.4%

+1 and -8 dB of a standard 6-dB per octave de-emphasis curve from 300 to 3000 Hz (1000-Hz reference)

^{*}These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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WARNING -

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

General Electric MASTR Progress Line Receivers Types ER-42-F and H are double-conversion, superheterodyne FM receivers designed for operation on the 406-420 and 450-470 megahertz bands. The Type ER-42-F Receivers contain a standard oscillator with a frequency stability of $\pm 0.0005\%$, while the Type ER-42-H Receivers contain an Integrated Circuit Oscillator Module (ICOM) with a frequency stability of $\pm 0.0002\%$. Standard and ultra-high sensitivity (UHS) versions are available for both types.

The receivers are of single-unit construction and are completely housed in an aluminum casting for maximum shielding and rigidity. The top part of the casting contains the front end through the 1st low IF amplifier stages. The bottom portion of the casting contains the audio squelch board.

CIRCUIT ANALYSIS

The MASTR Progress Line Receiver is completely transistorized, using silicon transistors throughout for added reliability. Input leads to the receiver are indificually filtered by the 20-pin feed-through by-pass connector J443. A regulated +10 volts is used for all receiver stages except the audio PA stage which operates from the 12-volt system supply.

Centralized metering jack J442 is provided for use with General Electric Test Set Models 4EX3A10 or 4EX8K11, for ease of alignment and servicing. The Test Set meters the oscillator, multiplier, and limiter stages as well as the discriminator, and regulated 10 volts.

RF AMPLIFIER (A410/A411)

RF Amplifier A410/A411 is used only in ultra-high sensitivity (UHS) receivers and consists of two tuned helical resonators and an RF amplifier (Q1).

RF from the antenna is coupled through cable W444 to a tap on L410/L412. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to L411/L413 through an opening in the shield wall, and then to the base of Q1.

The amplified output is taken from the collector of Q1 and coupled through cable W445 to the input of five helical resonators.

HELICAL RESONATORS

In receivers without the UHS option, the front end RF selectivity is provided by five tuned helical resonators (L414/L419 through L418/L423). RF cable W441 connects the RF signal from the antenna to a tap on

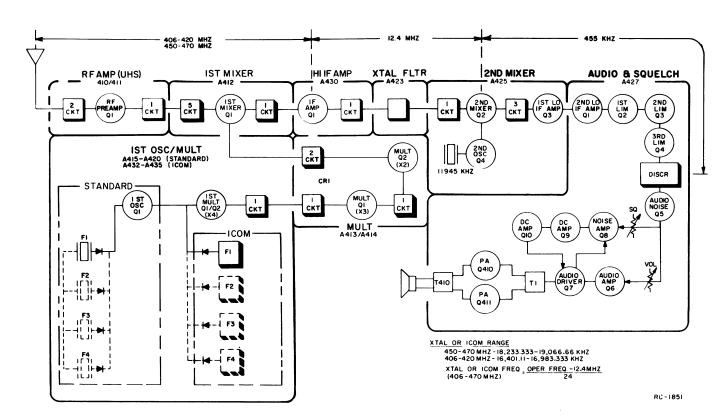


Figure 1 - Receiver Block Diagram

L414/L419. The tap is positioned to provide the proper impedance match to the antenna. The output of L418/L423 is coupled through capacitor C1 to the 1st mixer assembly.

1ST OSCILLATOR AND MULTIPLIER

Receiver Models 4ER42F10-27 are equipped with standard Oscillator/Multiplier Boards A415-A420. Receiver Models 4ER42H10-27 are equipped with Oscillator/Multiplier Boards which use the Integrated Circuit Oscillator Module (ICOM).

Standard Oscillator/Multiplier Board (A415-A420)

The oscillator in the standard Oscillator/Multiplier Board is a transistorized Colpitts oscillator. The oscillator crystal operates in a fundamental mode at a frequency of approximately 16 to 19 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides instant warm-up with a frequency stability of ±0.0005% without crystal ovens or warmers.

In single-frequency receivers, a jumper from H1 to H2 connects regulated +10 volts to the crystal circuit. Feedback for the oscillator is developed across C47.

In multi-frequency receivers, a diode is connected in series with the crystal and up to three additional crystal circuits can be added. The 10-volt jumper is removed, and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit. Switching the +10 volts to the crystal circuit forward biases the diode in series with the desired crystal, and the crystal frequency is applied to the base of oscillator transistor Q1. The oscillator output is coupled through C45 to the base of 1st Multiplier Q2.

The 1st multiplier output is coupled through T1/T2 to Multiplier Board A413/A414. T1/T2 is tuned to four times the crystal frequency. The 1st multiplier stage is metered at J442-4 through metering network C38, CR6, R17 and R18.

Oscillator/Multiplier Board With ICOM (A432-A435)

Oscillator/Multiplier Boards A432-A435 uses ICOM Module Model 4EG26A10. The ICOM module consists of a crystal-controlled Colpitts oscillator, a voltage regulator, and a buffer output stage. The entire module (including crystal) is enclosed in a dust-proof aluminum can, with the ICOM frequency and the receiver operating frequency printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature range to provide instant frequency compensation, with a frequency stability of $\pm 0.0002\%$ without crystal ovens or warmers.

In single-frequency receivers, +10 volts for operating the ICOM is obtained by a jumper from H1 to H2. With the ICOM operating, diode CR1 is forward biased and the oscillator output is applied to the 1st multiplier O1.

The 1st multiplier output is coupled through T1/T2 to multiplier board A413/A414. T1/T2 is tuned to four times the ICOM frequency. The 1st multiplier stage is metered at J442-4 through metering network C4, CR5, R5 and R6.

In multi-frequency receivers, up to three additional ICOM modules can be plugged into the board. The 10-volt jumper is removed and the proper frequency is selected by switching the desired ICOM to +10 volts by means of a frequency selector switch on the control unit.

-CAUTION-

All ICOM modules are individually compensated at the factory, and cannot be repaired in the field. Any attempt to remove the ICOM cover will void the warranty.

MULTIPLIER BOARD (A413/A414)

Following the oscillator board are two multiplier stages. A413-Q1 operates as a tripler, and Q2 operates as a doubler. Q2 is metered at J442-1 across metering resistor R6.

The output of Q2 is coupled through two helical resonator circuits to the source terminal of the 1st mixer. The helical resonators are tuned to six times the 1st multiplier output for a total multiplication of 24 times the crystal frequency.

1ST MIXER (A412)

The 1st Mixer uses a Field-Effect Transistor (FET) as the active device. A

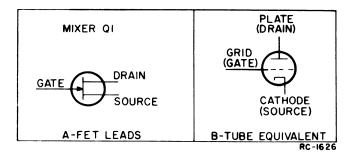


Figure 2 - FET Nomenclature

FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 2A. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 2B).

The FET mixer has several advantages over a conventional transistor mixer, including a high input impedance and an output that is relatively free of harmonics (low in intermodulation products).

RF from the helical resonators is applied to the gate of Ql, and injection voltage from the multiplier is applied to the source. The mixer output is taken from the drain with the output tuned to the 12.4 MHz high IF frequency.

HI IF AMPLIFIER (A430) AND CRYSTAL FILTER (A423)

The mixer output is coupled to the emitter of the high IF amplifier A430. The transistor is connected as a grounded-base amplifier which provides a low impedance for the mixer input. The amplifier output is coupled through transformer T1 to the crystal filter.

Highly-selective crystal filter A423 provides the major selectivity for the receiver. The output of the filter is coupled through impedance-matching transformer A425-T2 to the base of the 2nd mixer.

2ND OSCILLATOR, 2ND MIXER AND 1ST LO IF AMPLIFIER (A425)

A 425-Q4 operates in a Colpitts oscillator circuit, with feedback supplied through C18. The oscillator low-side injection voltage (11,945 kHz) is applied to the base of the 2nd mixer.

The High IF signal from the filter and the injection voltage from the 2nd oscillator is applied to the base of 2nd mixer Q2. The 445-kHz mixer output is applied to three tuned low IF circuits, L1, L2 and L3. These tuned circuits are required for shaping the nose of the IF waveform, and for rejecting any undesired output frequencies from the 2nd mixer.

The low IF signal is applied to the base of 1st low IF amplifier Q3. The output of Q3 is R-C coupled to the base of the 2nd low IF amplifier.

2ND LO IF AMPLIFIER AND LIMITERS (A427)

Additional amplification of the low IF signal going to the limiter stages is provided by 2nd low IF amplifier A427-Q1. This stage is metered at J442-2 through a metering network consisting of C19, CR3 and R25.

Following the 2nd low IF amplifier are three R-C coupled limiter stages (A427-Q2, -Q3 and -Q4). The 1st limiter is metered at J442-3 through metering network C20, CR4 and R26.

DISCRIMINATOR (A427)

The limiter output is applied to a Foster-Seely type discriminator, where diodes CR1 and CR2 rectify the 455-kHz signal to recover the audio. The discriminator is metered at J442-10 through metering network C44 and R23.

AUDIO - NOISE AMPLIFIER (A427)

The discriminator output is coupled through a low-pass filter (C44, C45, R68 and R69) to the base of audio-noise amplifier Q5. The filter removes any 455-kHz signal remaining in the discriminator outout. Q5 operates as an emitter-follower to match the discriminator impedance to the VOLUME and SQUELCH control. The stage also provides power gain.

AUDIO AMPLIFIERS (A427)

Any audio present in the incoming signal is coupled from the emitter of Q5 through the VOLUME control and a de-emphasis network to the base of audio amplifier Q6. The de-emphasis network consists of C22, C23. R30 and R31.

Audio driver Q7 follows the audio amplifier. The output of Q7 is coupled through transformer T1 to provide phase inversion for the push-pull audio PA stage.

Q410 and Q411 operate as a push-pull Class AB audio PA stage. The PA output is coupled through audio transformer T410 to the loudspeaker. The yellow and white tertiary windings of T410 supply balanced feedback to the collector of Q7. The feedback winding minimizes distortion and prevents the pick-up of external electrical noise.

Base bias for the PA stage and the elimination of crossover distortion is controlled by bias adjust potentiometer R43. The potentiometer is set at the factory as shown in STEP 1 of the receiver Test Procedure.

-NOTE---

Do not adjust bias adjust potentiometer R43 unless PA transistors Q410 and Q411 have been replaced.

Audio high and low are also present at centralized metering jack J442, and can be used as shown in STEP 1 of the receiver

Test Procedure. The output stage provides 5 watts at less than 5% distortion into a 3.5-ohm load at the receiver output terminals (3.2-ohm load at the Control Unit).

SQUELCH (A426)

Noise from the audio-noise amplifier operates the squelch circuit. With no carrier present in the receiver, this noise is coupled to the base of noise amplifier Q8 through a high-pass filter which attenuates frequencies below 3 kHz. The filter consists of C47, C48 and R71, as well as C46 and L3 in the collector circuit of Q8. The gain of Q8 is determined by the Squelch control, which varies the bias on the base of Q8. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

The output of noise amplifier Q8 is rectified by diodes CR5 and CR6, and filtered by C36 and C37 to produce a negative DC voltage. This DC voltage is applied to the base of DC amplifier Q9, turning it off. When turned off, the collector voltage of Q9 rises to approximately 8 volts, turning on DC amplifier Q10. When conducting, the collector voltage of Q10 drops to almost ground potential, which removes the base bias to audio amplifier Q6 and audio driver Q7, turning them off.

When the receiver is quieted by a signal (unsquelched), the noise in the receiver is reduced, turning DC amplifier Q9 on and DC amplifier Q10 off. This allows the audio stages to conduct so that sound is heard in the speaker. A network composed of C38, CR7 and R62 slows down the switching action of Q10, preventing an obnoxious "thump" from being heard in the speaker.

Resistor R73 connects from the emitter of audio driver Q7 to the emitter of noise amplifier Q8, providing a hysteresis loop in the squelch circuit. When a weak signal opens the squelch, the signal level may be reduced by 4 to 6 dB without the squelch closing. This limits squelch "flutter" or "picket-fence" operation.

With audio driver Q7 conducting, a positive voltage through R73 helps to reduce the gain of noise amplifier Q8. This positive feedback provides a quick, positive switching action in the squelch circuit.

When the receiver squelches, audio driver Q7. turns off and its emitter potential drops to zero. This reduces the DC feedback through R73 to the emitter of noise amplifier Q8. Reducing the feedback causes Q8 to conduct harder, turning the audio stages off quickly.

Keying the transmitter removes the +10 volts from J19, turning off DC amplifier Q9 and turning on Q10 to mute the receiver.

MAINTENANCE

DISASSEMBLY

To service the receiver from the top-

- 1. Pull locking handle down and pull radio about one inch out of mounting frame (see Fig. 3).
- 2. Pry up cover at rear of receiver.
- 3. Slide cover back and lift off.

To service the receiver from the bottom-

- Pull locking handle down. Pull radio out of mounting frame (see Fig. 4).
- Remove screws in bottom cover. Pry up cover at back of receiver.
- 3. Slide cover back and lift off.

To remove the receiver from the system frame—

- Loosen the two Phillips-head retaining screws in from casting (see Figure 3), and pull casting away from system frame.
- Remove the four screws in the back cover.
- Remove the two screws holding the receiver at each end of the system frame.
- 4. Disconnect the antenna jack and the 20pin connector from the front of the receiver, and slide the unit out of the system frame.

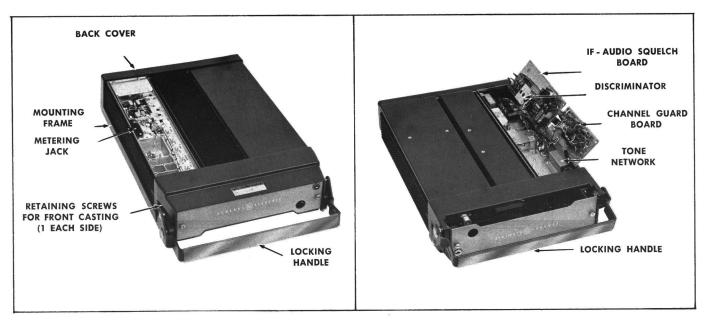
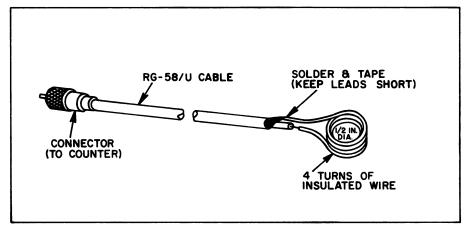


Figure 3 - Removing Top Cover

Figure 4 - Removing Bottom Cover



RC-1600

Figure 5 - Coaxial Cable and Test Loop

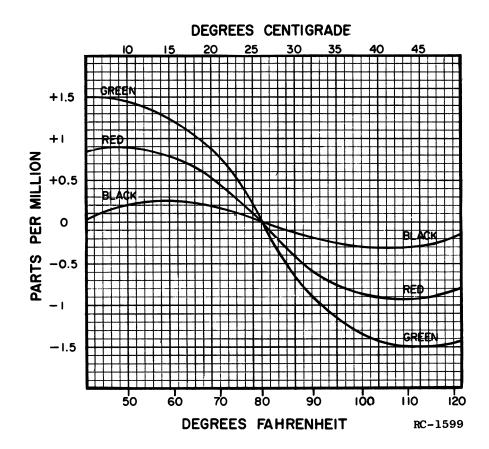


Figure 6 - ICOM Correction Curves

ALIGNMENT PROCEDURE __

406-470 MHz MASTR RECEIVER MODELS 4ER42F10-27 & 4ER42H10-27

FREQUENCY ADJUSTMENT

STANDARD OSCILLATOR

V	ulti-	MINING	METER	
	eter at J442	TUNING CONTROL	READING	PROCEDURE
A (Disc)	in 10	C9 (on 1st OSC/ MULT) C10, C11 and C12 for multi- frequency	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required. - NOTE - For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.

ICOM MODULE

Due to the high stability of the ICOM module, it is not recommended that zero discriminator be used as the indication for setting the oscillator frequency. Instead, measure the ICOM frequency as described in the following procedure.

EQUIPMENT REQUIRED:

- 1. Frequency Counter capable of measuring the 70-80 MHz frequency range. (The counter should have an accuracy of 0.4 part-per million.)
- 2. Coaxial cable with test loop as described in Figure 5.
- 3. Mercury thermometer.

PROCEDURE:

- 1. Check the ICOM temperature by taping the mercury thermometer to the side of
- 2. Connect the frequency counter to L5 (on the 1st Osc/Mult) using the 4-turn test loop and cable shown in Figure 5.
- 3. If the ICOM temperature is 80°F (±4°F) or 26.5°C (±2°C), the frequency indication on the counter should be 4 times the frequency stenciled on the ICOM case. Adjust the ICOM trimmer (if necessary) to obtain this frequency.
- 4. If the temperature is not within the 80°F (±4°F) or 26.5°C (±2°C) range, use the correction curves of Figure 6 for setting the ICOM frequency as follows:
- a. Check the color dot beneath the GE emblem and select the matching curve to determine the correction factor in parts-per-million (PPM).
- b. Multiply the frequency stenciled on the ICOM by 4 and then multiply this figure by the correction factor (from Figure 6) observing the sign (±) given to the correction factor.
- c. The frequency measured at L5 should be 4 times the ICOM frequency ± the correction factor. Adjust the ICOM trimmer (if required) to obtain this frequency.

FOR EXAMPLE	
ICOM Frequency - ICOM Color Dot - Ambient Temperature - Correction Factor - (From Figure 6)	18.233333 MHz Green 35°C (95°F) -1.15 PPM
Multiply ICOM Frequency by 4; (18.233333) MHz x $4 = 72.933332$	MHz)
Multiply preceding figure by c $(72.933 \text{ MHz x} -1.15 \text{ PPM} = -83.$	
Set the frequency measured at	L5 for 72.933248 MHz;
72.933332 MHz 000084 MHz 79.933248 MHz	

COMPLETE RECEIVER ALIGNMENT

EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3A10, 4EX8K11, station test meter panel, or 20,000 ohms-per-volt multimeter.
- 2. A 450 to 460 kHz source (GE Test Set Model 4EX7AlO), and 406-470 MHz signal source. Connect a one-inch piece of insulated wire no larger than .065 inch to

PRELIMINARY CHECKS AND ADJUSTMENTS

METERING POSITION

- 1. Connect Test Set to receiver centralized metering jack J442, and set meter sensitivity switch to the TEST 1 or 1-volt position.
- 2. For a large change in frequency or a badly mis-aligned receiver, set crystal trimmer C9 on 1st OSC/MULT board (ER-42-E only) to mid-capacity. In multi-frequency receivers, set C10, C11 or C12 to mid-capacity as required.
- 3. In multi-frequency receivers where the maximum frequency spacing is less than 500 kHz, align the unit on channel Fl. If the frequency spacing is greater than 500 kHz, align the receiver on the center frequency.
- 4. With Test Set in position J, check for regulated +10 volts. If using Multimeter, measure from C425 to C426.
- 5. If using Multimeter, connect the positive lead to J442-16 (ground)

ALIGNMENT PROCEDURE

GE Test Set Multimeter STEP or Meter Panel - at J442 TUNING CONTROL				METER READING	PROCEDURE					
				DISCRIMIN	ATOR					
1.	A (DISC)	Pin 10	L1 and L2 (on IF-AUDIO SQUELCH board)	Zero Remove three screws and swing open the IF-AUDIO & SQUELCH board. (disc primary) 1/2 turn counterclockwise from the bottom of coil. apply a 455-kHz signal to J2 and J4 and adjust L2 (disc secondary) meter reading.						
2.	A (DISC)	Pin 10		See Pro- cedure	Alternately apply a 450-kHz and 460-kHz signal and check for readings of a least 0.3 volt, but not more than 0.5 volt on GE Test Set. Both readings must be within .05 volt. Do not attempt to balance reading any closer tha 0.05 volt.					
OSCILLATOR AND MULTIPLIERS										
3.	D (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 (2nd MULT)	See Pro- cedure	Tune L5 for maximum meter reading. Then tune L1 for minimum meter reading.					
4.	G (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 and L2 (2nd MULT)	Maximum	Tune L5, L1 and L2 for maximum meter reading. If two peaks occur while tuning L1 and L2, use the peak with the slug nearest the top of the coil.					
5.	G (MULT-2)	Pin 4	C423	See Pro cedure	Adjust C423 for a small dip in meter reading.					
6.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal into Hole 411. Adjust the signal generator for discriminator zero.					
7.	(2nd IF AMP)	Pin 2	C423 and C424	Maximum	Apply an on-frequency signal as above. Tune C423 and C424 for maximum meter reading, keeping signal below saturation.					
				RF SELECTI	VITY					
8.	B (2nd IF AMP)	Pin 2	L3 (1st Mixer)	Maximum	Apply an on-frequency signal in Hole 411 and tune L3 for maximum meter reading. If two peaks occur, use the peak with the slug nearest the bottom of the coil.					
9.	B (2nd IF AMP)	Pin 2	C415 thru C418	Maximum	Apply an on-frequency signal in the Hole shown below, keeping the signal below saturation. Tune C415 thru C418 for maximum meter reading as shown below:					
					Insert Generator Probe In; Peak					
					1. Hole 411 C418 thru C417 2. Hole 410 C415, C416 thru C417					
10.	(2nd IF AMP)	Pin 2	C414 thru C418, L3 (on 1st Mixer) and C410, C411 and C7 (on UHS receivers)	See Pro- cedure	Apply an on-frequency signal to the receiver antenna jack. Tune C410, C411 and C7 on UHS receivers for maximum meter reading. On all receivers, tune C414 for maximum meter reading, and tune C415 thru C418 and L3 for maximum quieting.					
				2ND MIXER &	HI IF					

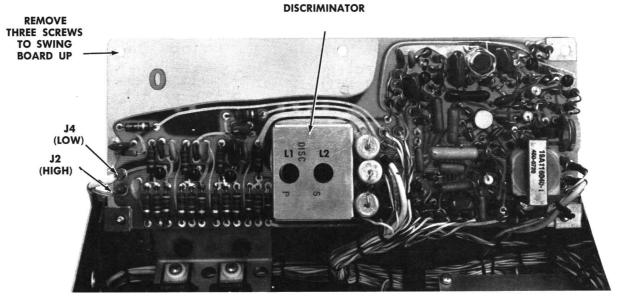
The 2nd mixer, and high IF circuits have been aligned at the factory and will normally require no further adjustment. If adjustment is necessary use the procedure outlined in STEPS 11, 12 and 13.

Refer to DATAFILE BULLETIN 1000-6 IF Alignment of Two-Way Radio FM Receivers for helpful suggestions on how to determine when

	L IF all	gument is req	uirea.		
1.	B (2nd IF AMP)	Pin 2	L3, L2, L1, T2 (2nd Mixer) and T1 (Hi IF AMP)	Maximum	Apply an on-frequency, unmodulated signal and tune L3, L2, L1, T2 (2nd mixer) and T1 (Hi IF AMP) for maximum meter reading, keeping signal below saturation.
			L3, L2, L1, T2 (2nd Mixer) and T1 (Hi IF AMP)		Connect scope, signal generator, and detector as shown in Figure 7. Set signal generator level for 30-50 µv and modulate with 20 kHz at 20 Hz. With detector at the collector of Q3 (2nd mixer board output), tune for double trace as shown on scope pattern. NOTE When using an M-560 signal generator, sufficient deviation may be obtained by setting the band switch on a lower scale.
13.	A (BISC)	Pin 10		See Pro- cedure	Check to see that discriminator idling voltage is within 0.1 volt of zero with no signal applied. Check to see that modulation acceptance bandwidth is between ±19 and 23 kHz.
			1	FREQUENCY ADJU	ISTMENT
14.	Refer to the	appropriate	adjustment procedure for the ICOM	or Standard Os	cillator.

1ST OSC/MULT. (ER-42-E) 1ST OSC/MULT. (ER-42-G) 2ND MULT. C12 C11 C10 C9 METERING F4 F3 F2 F1 **JACK** L5 ADJ ADJ ADJ ADJ (F3 F2 F1 F4) C425 C426 RF SELECTIVITY 2ND MIXER

IF-AUDIO & SQUELCH



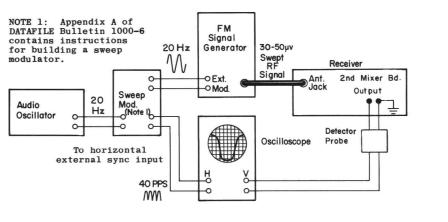


Figure 7 - Test Setup for 20-Hz Double-Trace Sweep Alignment

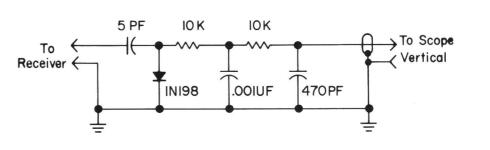


Figure 8 - Detector Probe for Sweep Alignment

FRONT END ALIGNMENT

LBI-4043

EQUIPMENT REQUIRED

- 1. GE Test Set Model 4EX3AlO, 4EX8Kll station test meter panel or 20,000 ohms-per-volt multimeter.
- 2. A 406-470 MHz signal source. Connedt a one-inch piece of insulated wire no larger than 0.065 inch to generator output probe.

PRELIMINARY CHECKS AND ADJUSTMENTS

METERING POSITION

- 1. Connect Test Set to receiver centralized metering jack J442 and set meter sensitivity switch to the TEST 1 (or 1-volt position on 4EX8K11).
- With Test Set in position J, check for regulated +10 volts. If using Multimeter, measure from
- 3. If using Multimeter, connect the positive lead to J442-16 (ground).

ALIGNMENT PROCEDURE

TEP	GE Test Set or Meter Panel		TUNING CONTROL	METER READING	PROCEDURE
			OSCILLATOR AND MULTI	PLIERS	
1.	D (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 (2nd MULT)	See Pro- cedure	Tune L5 for maximum meter reading. Then tune L1 for minimum meter reading.
2.	G (MULT-2)	Pin 4	L5 (1st OSC/MULT) and L1 and L2 (2nd MULT)	Maximum	Tune L5, L1 and L2 for maximum meter reading. If two peaks occur while tuning L1 and L2, use the peak with the slug nearest the top of the coil.
3.	G (MULT-2)	Pin 4	C423	See Pro- cedure	Adjust C423 for a small dip in meter reading.
4.	(DISC)	Pin 10		Zero	Apply an on-frequency signal into Hole 411. Adjust the signal generator for discriminator zero.
5.	B (2nd IF AMP)	Pin 2	C423 and C424	Maximum	Apply an on-frequency signal as above. Tune C423 and C424 for maximum meter reading, keeping signal below saturation.
	L		RF SELECTIVITY		
6.	B (2nd IF AMP)	Pin 2	L3, C415-C418	Maximum	Apply an on-frequency signal in Hole 411 and tune L3 and C415 thru C418 for maximum meter reading, keeping the signal below saturation. If two peaks occur when tuning L3, use the peak with the slug nearest the bottom of the coil.
7.	B (2nd IF AMP)	Pin 2	C414 thru C418, L3 (on 1st Mixer) and C410, C411 and C7 (on UHS receivers)	See Pro- cedure	Apply an on-frequency signal to the receiver antenna jack Tune C410, C411 and C7 on UHS receivers for maximum meter reading. On all receivers, tune C414 for maximum meter reading, and then tune C415 thru C418 and L3 for maximum quieting.
			FREQUENCY ADJUSTME	ENT	
8.	Refer to the	appropriate	adjustment procedure fo	or the ICOM or	Standard Oscillator.

ALIGNMENT PROCEDURE

406—470 MHz MASTR RECEIVER MODELS 4ER42F10-27 & 4ER42H10-27

Issue 1

LBI-4043

TEST PROCEDURES

These Test Procedures are designed to help you to service a receiver that is operating——but not properly. The problems encountered could be low power, poor sensitivity, distortion, limiter not operating properly, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized. Once

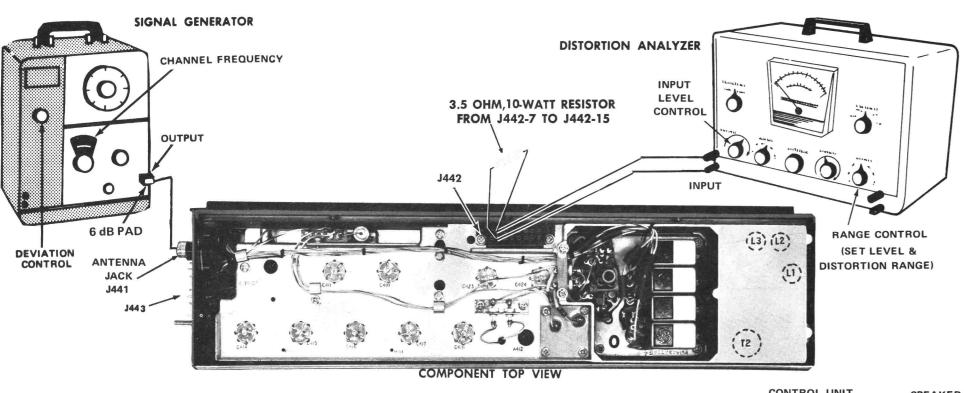
the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

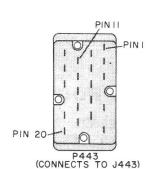
TEST EQUIPMENT REQUIRED

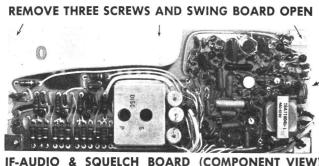
- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-800
- 6-dB attenuation pad, and 3.5-ohm, 10-watt resistor

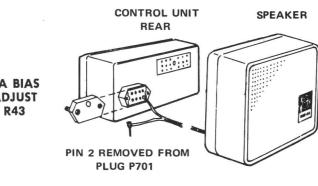
PRELIMINARY ADJUSTMENTS

- 1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure.
- 2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
- 3. Turn on all of the equipment and let it warm up for 20 minutes.









STEP 1 AUDIO POWER OUTPUT AND DISTORTION

TEST PROCEDURE

Measure Audio Power Output as follows:

- A. Apply a 1,000-microvolt, on-frequency test signal modulated by 1,000 hertz with ±10 kHz deviation to antenna jack J441.
- B. With Five-Watt Speaker:

Disconnect speaker lead pin from J701-2 (on rear of Control Unit).

Connect a 3.5-ohm load resistor from J442-15 to J442-7. Connect the Distortion Analyzer input across the resistor as shown.

U

With Handset:

Lift the handset off of the hookswitch Connect the Distortion Analyzer input from J442-15 to J442-7.

- C. Adjust the VOLUME control for five-watt output (4.18 VRMS using the Distortion Analyzer as a VTVM).
- D. Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%. If the receiver sensitivity is to be measured, leave all controls and equipment as they are.

SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than five watts, make the following checks:

- Battery and regulator voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- F. P.A. Bias Adjust (R43) -- Turn the SQUELCH control fully counterclockwise.

Then connect a milliammeter in series with the +12 volt lead at P443-11. With no signal in, adjust R43 for a reading of approximately 20 milliamps. This adjustment should not be necessary unless an output transistor has been rereplaced.

- G. Audio Gain (Refer to Receiver Trouble-shooting Procedure).
- H. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

STEP 2 USABLE SENSITIVITY (12-dB SINAD)

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

- A. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.0-KHz deviation to J441.
- Place the RANGE switch on the Distortion Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.)
- C. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).
- D. While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).
- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specification with an audio output of at least 2.5 watts (2.9 volts RMS across the 3.5-ohm receiver load using the Distortion Analyzer as a VTVM).

F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be performed.

SERVICE CHECK

If the sensitivity level is more than rated 12 dB SINAD, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

STEP 3 MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH)

If STEPS 1 and 2 check out properly, measure the bandwidth as follows:

- Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.
- Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.
- C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).
- D. The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ±19 kHz (but less than ±23 kHz).

SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

STEP I - QUICK CHECKS

TEST SET CHECKS

These checks are typical voltage readings measured with GE Test Set Model 4EX3A10 in the Test 1 position, or Model 4EX8K11 in the 1-volt position.

4EXSKII IN the	1-voit position.	
Metering Position	Reading with No Signal in	Reading with 1 μν unmodulated input
A Disc idling	Less than ±0.1 VDC	
B 2nd IF	.05 VDC	0.2 VDC
C 1st Lim	0.6 VDC	0.8 VDC
D Mult 1	0.9 VDC	
G Mult 2	0.3 VDC	
J Regulated +10 Volts	10 VDC	

SYMPTOM CHECKS

				
SYMPTOM	PROCEDURE			
NO SUPPLY VOLTAGE	Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.			
NO REGULATED 10-VOLTS	• Check the 12-volt supply. Then check regulator circuit (See Troubleshooting Procedure for Power Supply).			
LOW 1ST LIM READING	 Check supply voltages and then check oscillator reading at J442-4 & 5 as shown in STEP 2A. 			
	Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 1st Limiter stages as shown in STEP 2A.			
LOW OSCILLATOR/MULTI- PLIER READINGS	 Check alignment of Oscillator (Refer to Front End Alignment Procedure). 			
	Check voltage readings of 1st Oscillator/Multiplier Q1/Q2.			
	• Check crystal Yl.			
LOW RECEIVER SENSITIVITY	Check Front End Alignment (Refer to Receiver Alignment Procedure).			
	Check antenna connections, cable and relay.			
	• Check 1st and 2nd Oscillator injection voltage.			
	• Check voltage readings of RF Amp, 1st Mixer and HI IF Amp.			
	Make SIMPLIFIED GAIN CHECKS (STEP 2A).			
LOW AUDIO	• Check Audio PA (Q410 & Q411) voltage readings on schematic diagram.			
	Make simplified gain and waveform checks of audio and squelch stages (Steps 2A and 2B).			
	Make unsquelched voltage readings in Audio section (Refer to Receiver Schematic Diagram).			
HIGH DISTORTION AT LOW AUDIO LEVELS (50 MW)	Set PA bias adjust R43 as specified under Service checks in STEP 1 of TEST PROCEDURES.			
IMPROPER SQUELCH OPERATION	• Check voltage readings of Squelch circuit (Refer to Receiver Schematic Diagram).			
	 Make gain and waveform checks of audio and squelch stages (Steps 2A and 2B). 			
DISCRIMINATOR IDLING TOO FAR OFF ZERO	See if discriminator zero is in center of IF bandpass.			

STEP 3-VOLTAGE RATIO READINGS —— 406-470 MHZ 406-470 MHZ 406-470 MHZ 406-470 MHZ

EQUIPMENT REQUIRED:

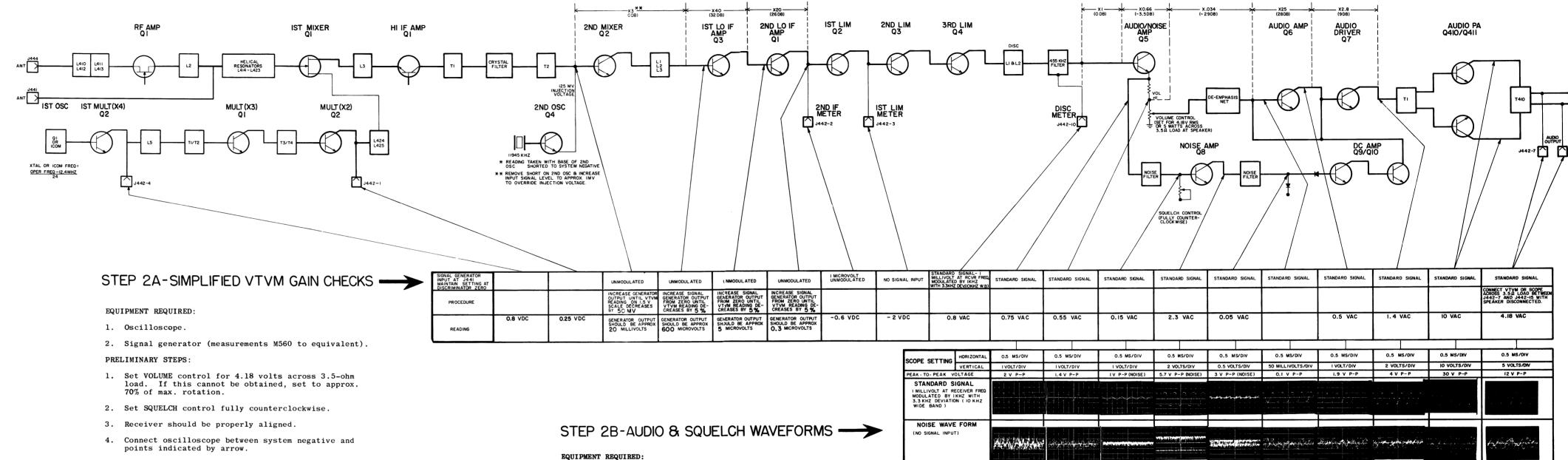
- RF Voltmeter (Similiar to Boonton Model 91-CA or Millivac Type MV-18 C).
- Signal on receiver frequency (below saturation). Correct frequency can be determined by zeroing the discriminator. Use 1,000 Hertz signal with 10 kHz deviation for audio stage.

PROCEDURE

- 1. Apply probes to input of stage and system negative (-10 VDC). Take voltage reading (E_1) .
- 2. Move probes to input of following stage and system negative. Take reading (E_2) .
- 3. Convert readings by means of the following for-

Volatge Ratio = $\frac{E_2}{E_1}$

 Check results with typical voltage ratios shown on diagram.



1. VTVM-AC & DC

2. Signal Generator (measurements M560 or equiv.)

ELIMINARY STEPS:

- Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- Connect VTVM between system negative and points indicated by arrow (except for 1st MULT which references chassis ground).

RC-1828B

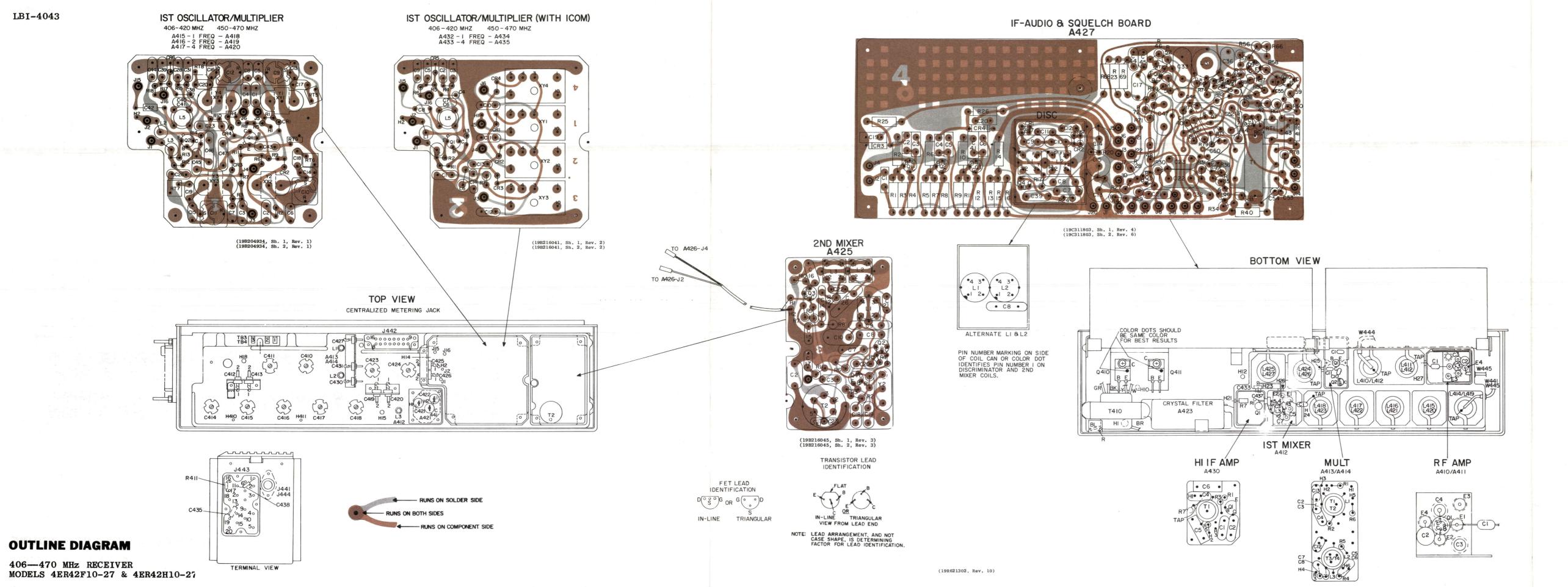
TROUBLESHOOTING PROCEDURE

406—470 MHz RECEIVER MODELS 4ER42F10-27 & 4ER42H10-27

Issue 2

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LBI-4043



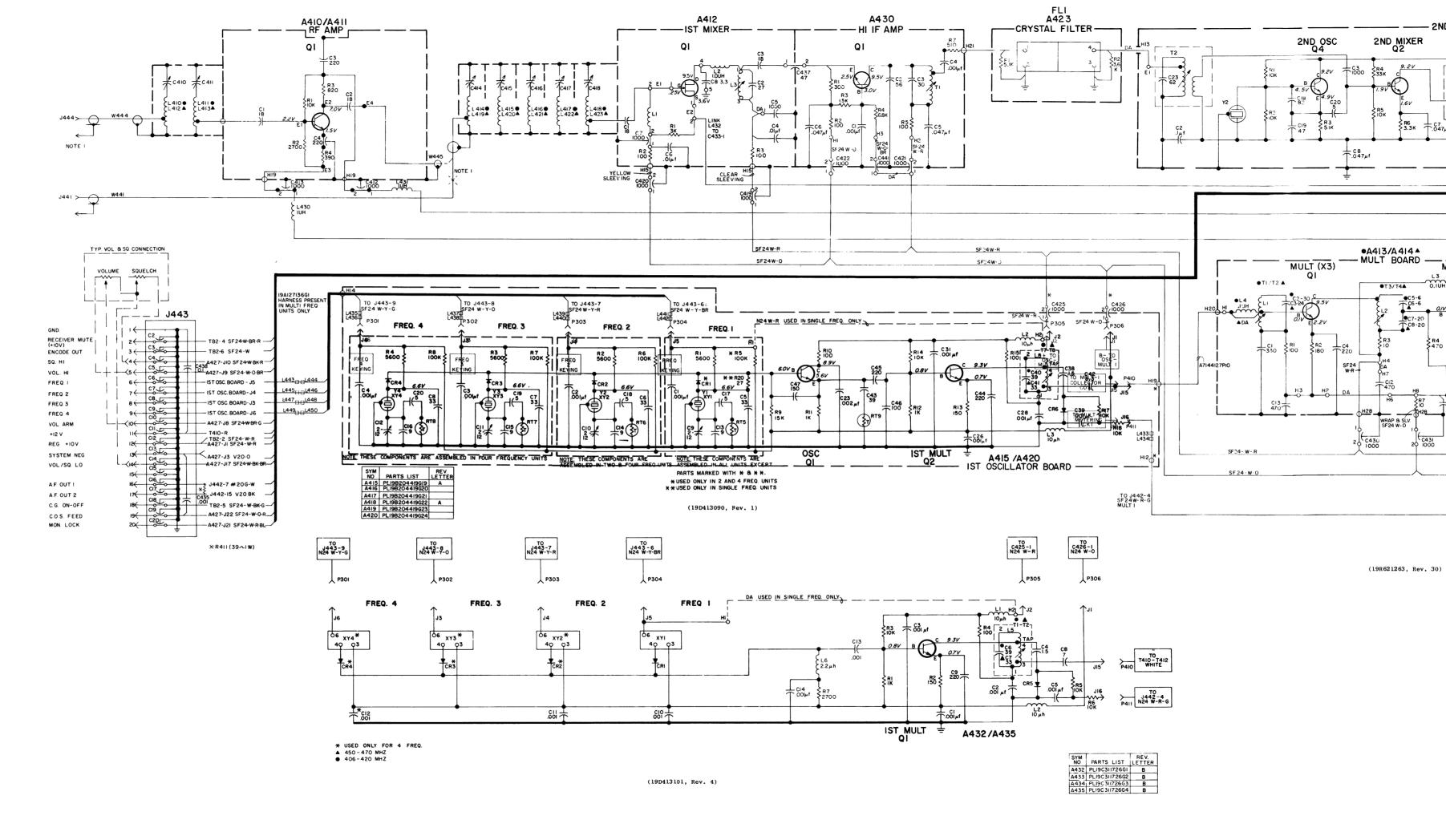
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LBI-4043

	PARTS LIST	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
	LBI-4049B	C2	7484398P3	Silver mica: 250 pf ±10%, 500 VDCW; sim to			TRANSISTORS	сз	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp	C31	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	C41	5496218P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef	L2	19A115711P1	Transformer, freq: 455 KHz; sim to Automat
	06-470 MHz RECEIVERS R42F10-27, 4ER42H10-27	сз	5493392P7	Underwood Type J1HF.	Q1	19A116154P1	N Channel, field effect.			coef -80 PPM.			RMC Type JF Discap.	(41	3430216F231	-80 PPM.	and L3		Mfg EX12670.
				Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FA5C.			RESISTORS				C38	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW; sim to Quality Components Type MC.			INDUCTORS			
		C4	5493392P107	Ceramic, stand-off: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type SS5D.	R1	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.	L1 L4	19B216373P5 19B209420P1	Coil. RF: 0.10 µh ±5%, 0.08 ohms DC res max;	c39	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	L5	19A121728P1	Coil. Includes tuning slug 5491798P5.	P1 P2	4029840P2 4029840P1	Contact, electrical: sim to Amp 42827-2. Contact, electrical: sim to Amp 41854.
SYMBOL GE PART NO.	DESCRIPTION	C5	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	R2 and	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	14		sim to Jeffers 4416-1.	C42	5491601P130	Phenolic: 3.3 pf ±5%, 500 VDcW; sim to Quality Components Type MC.			SOCKETS	PZ	4029840P1	
		C6	5491601P124	Phenolic: 1.8 pf ±5%, 500 VDCW.	R3				5491798P7	Tuning slug.	C43	5496219P53	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef	XY1 thru		Refer to Mechanical Parts (RC-1823).			
1410*	RF AMPLIFIER 19c320697G1	C7	7484389P1	Variable: 1.5-7 pf, temp coef 0 PPM; sim to Erie Style 503.	A413 and		MULTIPLIER BOARD ASSEMBLY A413 19B216360G1	and T4		COIL ASSEMBLY T3 198216374G1 T4 198216374G2	C44	5490008P135	0 PPM. Silver mica: 220 pf ±10%, 500 VDCW; sim to	XY4			Q2 Q3	19A115245P1 19A115123P1	Silicon, NPN. Silicon, NPN; sim to Type 2N2712.
and A411*		C8	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.	A414		A414 19B216360G2						Electro Motive Type DM-15.			NOTE: When reordering give GE Part No. and	Q4	19A115245P1	Silicon, NPN.
c1 5496218 P24 5				TERM INALS				C5*	5496218P237	CAPACITORS	C45	5490008P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.			specify exact freq needed.			RESISTORS
and C2	-80 PPM.	El	19B209055P1	Terminal, feed-thru: sim to Electrical Ind.	C1	19A116655P12	Ceramic disc: 330 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			coef -80 PPM.	C46	5496219P563	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -330 PPM.			Crystal freq = (<u>OF -12.4</u> MHz) 24	R1	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
C3 5493392P105	Ceramic, stand off: 220 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.			ABAS-40W-RR.	C2		(Part of T1).		5496218P439	In REV F and earlier: Ceramic disc: 8 pf ±0.25 pf, 500 VDCW, temp	C47	5496219P767	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef	Y1	19B206576P6	Quartz: freq range 15175.000 to 17925.000 KHz, temp range -30°C to +85°C. (405-420 MHz)	and R2		
C4 5493392P5	Ceramic, feed-thru: 220 pf +100% -0%, 500 VDCW;			INDUCTORS	с3		(Part of T2).			coef -220 PPM.			-130 PPM.	thru Y4		temp range -30 C to +65 C. (405-420 mn2)	R3	3R77P512J	Composition: 5100 ohms ±5%, 1/2 w.
	sim to Allen-Bradley Type FA5C.	L1	19B209420P1	Coil, RF: 0.10 μh $\pm 5\%$, 0.08 ohms DC res max; sim to Jeffers 4416-1.	C4	5496203P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.	C6*	5496218P237	Ceramic disc: 6 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.			DIODES AND RECTIFIERS	A423		CRYSTAL FILTER ASSEMBLY	R4 R5	3R152P333K 3R152P103J	Composition: 33,000 ohms ±10%, 1/4 w. Composition: 10,000 ohms ±5%, 1/4 w.
		L2	19A127429P1	Coil.	C 5		(Part of T3).			In REV G and earlier:	CR1 thru CR4	19A115603P1	Silicon.			19821670301	R6	3R77P332K	Composition: 3300 ohms ±10%, 1/2 w.
El 19B209055P8 and	Terminal, feed-thru: sim to Electrical Ind. ABAS40WSS.	L3	19A127429P2	Coil.	C6		(Part of T4).		5496218 P43 6	Ceramic disc: 5 pf ±0.25 pf, 500 VDCW, temp coef -220 PPM.	CR6	19A115250P1	Silicqn.				R7	3R77P123K	Composition: 12,000 ohms $\pm 10\%$, $1/2$ w.
E2 E3 19B209055P1	Terminal, feed-thru: sim to Electrical Ind.			TRANSISTORS	C7		(Part of T3). (Part of T4).	C7*	5496218P746	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -750 PPM.			; 	FL1	19C3O4O94G5	Bandpass, 12.4 MHz.	R8	3R77P622J	Composition: 6200 ohms ±5%, 1/2 w.
15820500071	ABAS-40W-RR.	Q1	19A116154P1	N Channel, field effect.	C9*	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to		1	In REV F and earlier:	J1	4033513P4	Contact, electrical: sim to Bead Chain L93-3.				R9	3R77P302J	Composition: 3000 ohms ±5%, 1/2 w.
E4 19B209055P8	Terminal, feed-thru: sim to Electrical Ind. ABAS40WSS.			RESISTORS	c10	5496203P149	RMC Type JF Discap. Deleted by REV E. Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef		5496218 P75 0	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -750 PPM.	thru J6			Rl	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	R10 R11	3R77P202J 3R77P201J	Composition: 2000 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w.
		R1 and	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		1	-3300 PPM.	C8*	5496218P246	Ceramic disc: 20 pf ±5%, 500 VDCW, temp	J15 and	4033513P4	Contact, electrical: sim to Bead Chain L93-3.			RESISTORS	R12	3R77P513J	Composition: 51,000 ohms ±5%, 1/2 w.
Q1 19A116859P1	Silicon, NPN; sim to Type 2N5032.	R2	3R152P470K	Composition: 47 ohms ±10%, 1/4 w.	c11	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.			coef -80 PPM. In REV G:	J16			R1	3R152P512J	Composition: 5100 ohms ±5%, 1/4 w.			TRANSFORMERS
			5R1021 110R		C12	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.		5496218P745	Ceramic disc: 18 pf ±5%, 500 VDCW, temp	L2	7488079P16		R2	3R152P362J	Composition: 3600 ohms ±5%, 1/4 w.	т2		COIL ASSEMBLY
R1 3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	A412		FIRST MIXER ASSEMBLY 19C311974G1	c13	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim			coef -750 PPM. In REV F and earlier:	and L3	1.000.0120	DC res; sim to Jeffers 4421-7K.	A425		SECOND MIXER ASSEMBLY 19B216119G2			19B216120G2
R2 3R152P272J	Composition: 2700 ohms $\pm 5\%$, $1/4$ w.			CAPACITORS	C14	5496218P548	to RMC Type JF Discap. Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef		5496218P748	Ceramic disc: 24 pf ±5%, 500 VDCW, temp						CAPACITORS			CAPACITORS
R3 3R152P821J	Composition: 820 ohms ±5%, 1/4 w.	C1	5496218P312	Ceramic disc: 18 pf ±10%, 500 VDCW, temp		ł	-330 PPM.			coef -750 PPM.	Q1 and	19A115330P1	Silicon, NPN.	C2	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDcW.	C23	5496218P258	Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef -80 PPM.
R4 3R152P391J	Composition: 390 ohms ±5%, 1/4 w.	C2		coef -150 PPM. (Part of L3).	c15*	5494481P7	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV C.				Q2		RESISTORS	с3	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.		5491798P3	Tuning slug.
	In 19E500881G7 REV G-L: In 19E500881G8 REV G-M:	C3*	5496218P344	Ceramic disc: 15 pf ±5%, 500 VDCW, temp				L2	19B216374P5	Coil. (Used with low split).	Rl	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	C7	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.			
10* d	RF AMPLIFIER 19C317950G1			coef -150 PPM. In 19E500881G5 REV L and earlier:	Ll		(Part of Tl and T2).		19B216374P7 5491798P7	Coil. (Used with High split). Tuning slug.	thru R4	1		and C8			Y2	19A110398P1	Quartz: freq 11945.00 KHz, temp range -30 +75°C.
ĭ1*				In 19E500881G6 REV M and earlier: In 19E500881G7 REV M and earlier:	L2		(Part of T3 and T4).			FIRST OSCILLATOR ASSEMBLY	R5 thru	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.	С9	5496219P369	Ceramic disc: 180 pf $\pm 5\%$, 500 VDCW, temp coef -150 PPM.			IF AUDIO AND SQUELCH BOARD
C1 5496218P245			5496218P249	In 19E500881G8 REV N and earlier: Ceramic disc: 27 pf ±5%, 500 VDCW, temp	L3	19B209420P1	Coil, RF: 0.10 μh $\pm 5\%$, 0.08 ohms DC res max; sim to Jeffers 4416-1.	A415 thru A420		A415 19B204419G19 A416 19B204419G20	R8	3R152P153J	Composition, 15 000 object +5% 1/4 w	C10	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	A427		19D413129G2
and C2	-80 PPM.			coef -80 PPM.	L4		(Part of Tl).			A417 19B204419G21 A418 19B204419G22	R10	3R152P153J 3R152P101K	Composition: 15,000 ohms ±5%, 1/4 w. Composition: 100 ohms ±10%, 1/4 w.	C14	19A116656P220J2	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -220 PPM.			
C3 5493392P5	Ceramic, feed-thru: 220 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.	C4 C5	19A116080P1 5493392P107	Polyester: 0.01 µf ±20%, 50 VDCW. Ceramic, stand-off: 1000 pf +100% -0%, 500 VDCW.			TRANSISTORS			A419 19B204419G23 A420 19B204419G24	R11	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	C15	7491395P109	Ceramic disc: 1000 pf ±10%, 500 VDCW; sim to RMC Type JL.	c1	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; si
C4 5493392P107	Ceramic, stand off: 1000 pf +100% -0%, 500			sim to Allen-Bradley Type SS5D.	Q1	19A115329P1	Silicon, NPN.				and R12			c16	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.	C2	5496219P717	Ceramic disc: 47 pf ±10%, 500 VDCW, temp
thru C6	VDCW; sim to Allen-Bradley Type SS5D.	C6	19A116080P1 5493392P7	Polyester: 0.01 µf ±20%, 50 VDCW. Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW;	Q2	19A115991P1	Silicon, NPN.	C1	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R13	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.	c17	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDcW.	сз	5494481P111	-750 PPM. Ceramic disc: 1000 pf ±20%, 1000 VDCW; si
			013333211	sim to Allen Bradley Type FA5C.			RESISTORS	thru C4			R14	3R152P103J 3R152P101K	Composition: 10,000 ohms ±5%, 1/4 w. Composition: 100 ohms ±10%, 1/4 w.	C18	5490008P25	Silver mica: 82 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.			RMC Type JF Discap.
L1 19B209420P1 and L2	Coil, RF: 0.10 μh $\pm 5\%,$ 0.08 ohms DC res max; sim to Jeffers 4416-1.	C8		(Part of L3).	R1	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	C5 thru	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.	R17	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	C19	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to	C4	5496219P717	Ceramic disc: 47 pf ±10%, 500 VDCW, temp -750 PPM.
L2 L3 19A116632P1	Torridal core.			TERM INALS	R2 R3	3R152P181J 3R152P100K	Composition: 180 ohms ±5%, 1/4 w. Composition: 10 ohms ±10%, 1/4 w.	C8	5491271P106	Variable, subminiature: approx 2.1-12.7 pf,	and R18			C20	5490008P1	Electro Motive Type DM-15. Silver mica: 5 pf ±0.5%, 500 VDCW; sim to	C5 and	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; si
thru L5	101111111111111111111111111111111111111	El and	19B209055P8	Terminal, feed-thru: sim to Electrical Ind. ABAS40WSS.	R4	3R152P471K	Composition: 470 ohms ±10%, 1/4 w.	thru C12		750 v peak; sim to EF Johnson 189.	R20	3R152P270K	Composition: 27 ohms $\pm 10\%$, $1/4$ w.			Electro Motive Type DM-15.	C6	10111500005	Polyester: 0.047 µf ±20%, 50 VDcW.
		E2		INDUCTORS	R5	3R152P680J	Composition: $68 \text{ ohms } \pm 5\%, \ 1/4 \text{ w}.$	C13 thru	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.		İ	THERMISTORS	C21 and C22	5496219P49	Ceramic disc: 27 pf ±5%, VDCW, 500 VDCW, temp coef 0 PPM.	cs cs	19A116080P5 19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp
Q1 19A116154P1	N Channel, field effect.	Ll	19A127430G1	Choke.	R6	3R152P273K	Composition: 27,000 ohms ±10%, 1/4 w.	C16	10000000505000	Constitution 5 of to 1 of 500 VDCW town	RT5 thru	19B209284P7	Disc: 62 ohms res nominal at 25°C, color code violet.	C23		(Part of T2).	C9	5490008P37	-150 PPM. Silver mica: 270 pf ±5%, 500 VDCW; sim to
		L2		(Part of L3).	R7*	3R152P100K	Composition: 10 ohms $\pm 10\%$, $1/4$ w. Added by REV C.	c17 thru c20	19C300685P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef 0 PPM.	RT8	19B209284P8	Disc: 945 ohms res nominal at 25°C, color	C26	5496219P368	Ceramic disc: 160 pf ±5%, 500 VDCW, temp coef -150 PPM.	and C10	5490008P37	Electro Motive Type DM-15.
R1 3R152P101K and	Composition: 100 ohms $\pm 10\%$, 1/4 w.	L3	19B216440G1	Coil assembly, includes:			TRANSFORMERS	C23	5494481P114	Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to	RT9	198209284P8	code gray.				C11	5496219P656	Ceramic disc: 51 pf ±5%, 500 VDcW, temp
R2	In REV F and earlier:	C2	5496218P249	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.	T1 and		COIL ASSEMBLY T1 19B216373G1	C26	5494481P112	RMC Type JF Discap. Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to					4033513P4		C12	5494481P108	-470 PPM. Ceramic disc: 470 pf ±10%, 1000 VDCW; sin
A410*	RF AMPLIFIER	L2	19B209420P113	Coil, RF: 1 $\mu h \pm 10\%$, 0.74 ohms DC res max; sim to Jeffers 4426-6.	T2		T2 19B216373G2			RMC Type JF Discap.	T7		COIL ASSEMBLY T7 19B204950G1	"	4033313P4				RMC Type JF Discap. Electrolytic: 100 µf +150% -10%, 15 VDCW
and A411*	A410 19c311975G1 A411 19c311975G2		5491798P8	Tuning slug.		1		C28	5494481P112	Ceramic disc: 1000 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.	Т8		T8 19B204950G2		19C311181G3	INDUCTORS	C13	19A115680P107	Electrolytic: 100 µf +150% -10%, 15 VDCW to Mallory Type TT.
	CAPACITORS				C2	5496218P350	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -150 PPM.							Li	19031118163	Coil assembly.			
Cl 5493392P107	Ceramic, stand-off: 1000 pf +100% -0%, 500 VDCW: sim to Allen-Bradley Type SS5D.								1.		C44	0 5496218P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.				[]		
	THER, SIM to Allen-Brautey type 3300.											1							1
																		1	

DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
freq: 455 KHz; sim to Automatic	C14 and C15	19A115680P104	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim to Mallory Type TT.
PLUGS	c17	19A116080P7	Polyester: 0.1 μf ±20%, 50 VDcW.
ctrical: sim to Amp 42827-2.	C19	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.
ctrical: sim to Amp 41854.	and C20		
TRANSISTORS	C21	19A116080P3	Polyester: 0.01 µf ±20%, 50 VDCW.
	C22	19A116080P108	Polyester: 0.15 μf ±10%, 50 VDCW.
; sim to Type 2N2712.	C23	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.
	C25	5496267P6	Tantalum: 33 μf $\pm 20\%$, 10 VDCW; sim to Sprague Type 150D.
RESISTORS	C26*	19A116080P110	Polyester: 0.33 μf ±10%, 50 VDCW. In REV E-L:
10,000 ohms ±10%, 1/2 w.		19A116080P109	Polyester: 0.22 μf ±10%, 50 VDCW.
5100			In REV D and earlier:
5100 ohms ±5%, 1/2 w. 33,000 ohms ±10%, 1/4 w.		5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Spragu
10,000 ohms ±5%, 1/4 w.	C27*	5496267 P 2	Type 150D. Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague
3300 ohms ±10%, 1/2 w.	C2/*	3490207P2	Type 150D.
12,000 ohms ±10%, 1/2 w.			In REV B and earlier:
6200 ohms ±5%, 1/2 w.		5496267 P 6	Tantalum: 33 μf $\pm 20\%$, 10 VDCW; sim to Sprague Type 150D.
3000 ohms ±5%, 1/2 w.	c32	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.
2000 ohms ±5%, 1/2 w.	c33	19A116080P9	Polyester: 0.22 μf ±20%, 50 VDcW.
: 200 ohms ±5%, 1/2 w.	C35	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDcW.
: 51,000 ohms ±5%, 1/2 w.	c36	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.
TRANSFORMERS	C37	5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.
COIL ASSEMBLY 19B216120G2	c38*	5496267P10	Tantalum: 22 μf $\pm 20\%$, 15 VDcW; sim to Sprague Type 150D. Deleted by REV C.
CAPACITORS	c39	19A116080P1	Polyester: 0.01 μf ±20%, 50 VDCW.
c: 62 pf ±5%, 500 VDCW, temp	C40*	5496267P29	Tantalum: 0.68 µf ±20%, 35 VDCW; sim to Sprague Type 150D.
٠.			In REV J and earlier:
		5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.
CRYSTALS	C41	5490008P129	Silver mica: 120 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
F AUDIO AND SQUELCH BOARD	C44	5494481P124	Ceramic disc: 1500 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
19D413129G2	C45	5490008P27	Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
CAPACITORS	C46	4029003P108	Silver Mica: 1000 pf ± 10%, 500 VDCW; sim to Electro Motive Type DM-20.
Discap.	C47	19A116080P9	Polyester: 0.22 μf ±20%, 50 VDCW.
c: 47 pf ±10%, 500 VDCW, temp coef	C48	19A116080P1	Polyester: 0.01 μf ±20%, 50 VDCW.
c: 1000 pf ±20%, 1000 VDCW; sim to Discap.	C49*	5496267P9	Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Spragu Type 150D. Deleted by REV C.
c: 47 pf ±10%, 500 VDCW, temp coef	C50	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.
c: 1000 pf ±20%, 1000 VDCW; sim to	C51	19A116655P22	Ceramic disc: 2700 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
Discap.	C52	19A116080P109	Polyester: 0.22 μf ±10%, 50 VDCW.
0.047 µf ±20%, 50 VDCW.	C53 and	5496267P213	Tantalum: 2.2 μf ±10%, 20 VDCW; sim to Spragu Type 150D.
c: 180 pf ±5%, 500 VDCW, temp coef	C54	5406927D14	Tentalum: 15 of +20% 20 VDCW sim to Sprague
: 270 pf ±5%, 500 VDcW; sim to ive Type DM-15.	C55*	5496267P14	Tantalum: 15 μf $\pm 20\%$, 20 VDCW; sim to Sprague Type 150D. Added by REV C.
c: 51 pf ±5%, 500 VDCW, temp coef	CR1	19A115250P1	DIODES AND RECTIFIERS Silicon.
c: 470 pf ±10%, 1000 VDCW; sim to Discap.	and CR2 CR3*	19A115250P1	Silicon.
c: 100 µf +150% -10%, 15 VDCW; sim	and CR4*		
Type TT.		40000000	In REV E and earlier:
		4038056P1	Germanium.

S WITH RETE CUIT LATOR	MODELS WITH ICOM OSCILLATOR	NO. OF FREQS	FREQ RANGE 406-420=L0 450-470=HI	U H S RECEIVER A410/A411 PRESENT
FIO	4 ER 42HIO	1	LO	
FII	4ER42H11	1	HI	
F 12		2	LO	
F13		2	HI	
F 14	4ER42HI4	4	LO	
F 15	4ER42HI5	4	HI	
				<u></u>
			+	
				<u> </u>
			<u> </u>	
F22	4ER42H22	1	LO	X
2F 23	4ER42H23	t	HI	X
F 24		2	L0	X
F 25		2	HI	X
F26	4ER 42H26	4	LO	х
F27	4ER42H27	4	HI	X



A 425 ----- 2ND MIXER BOARD ---- -----

TO J442 - I SF24W-BK-BL MULT 2

WRAP & SĹV. SF24 W-0

TB4-2 TO TR2-1 SYS.NEG

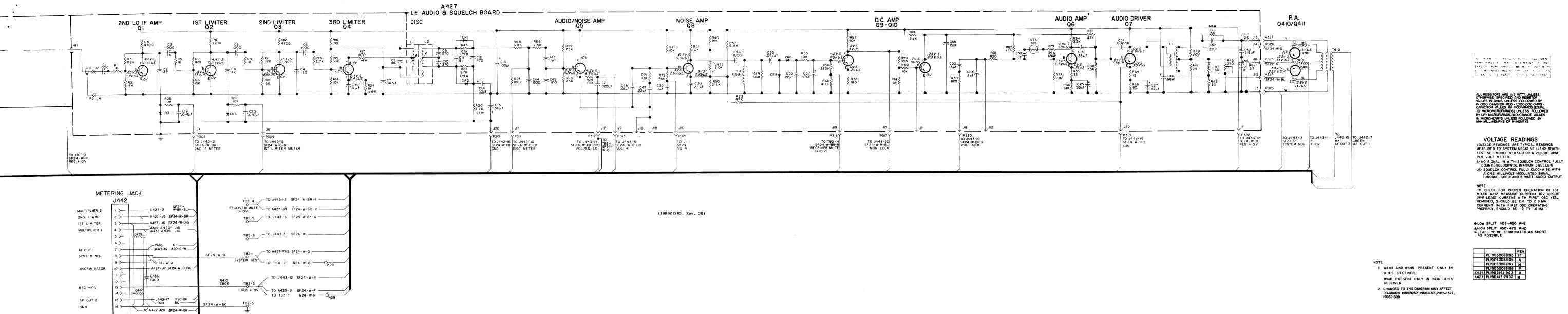
SF24W-R

- C429 + 50μf OTB4-1

DA STB4-MOUNTING

SCHEMATIC DIAGRAM

406—470 MHz RECEIVER MODELS 4ER42F10-27 & 4ER42H10-27



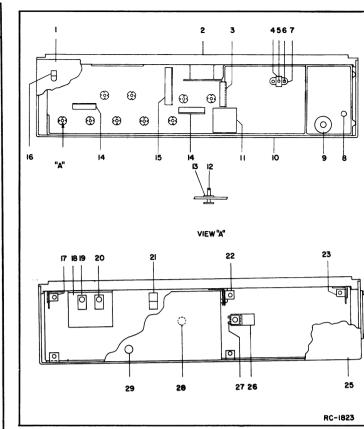
AF OUT 2

SF24-W-BK TB2-3

SCHEMATIC DIAGRAM

406—470 MHz RECEIVER MODELS 4ER42F10-27 & 4ER42H10-27

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	1
CR5	19A115250P1	Silicon,				R81*	3R152P472J	Composition: 4700 ohms ±5%, 1/4 w. Added by	C4	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW.				L425	19B204936P15	Coil.	L435 thru	19A115700P2	Bead, ferrite. (Part of 19Al27136G1 Harness assembly).	
and CR6	15.11.102.0011		R31	3R77P821J	Composition: 820 ohms ±5%, 1/2 w.			REV C.	C5	5494481P112	Ceramic disc: 1000 pf ±10%, 500 VDCW; sim			CHASSIS AND RF CIRCUIT 19E500881G5 thru G8	L426	19B204938G20	Coil.	L442		assembly).	
CR7*	19A115250P1	Silicon, Deleted by REV C.	R33	3R77P912J	Composition: 9100 ohms ±5%, 1/2 w.	R82*	3R77P273J	Composition: 27,000 ohms ±5%, 1/2 w. Added by REV C.			to RMC Type JF Discap.			arni arnon	L427	19B204936P16	Coil.	L443 thru	19A115700P2	Bead, ferrite.	
and CR8*		·	R35	3R77P332K 3R77P330K	Composition: 3300 ohms ±10%, 1/2 w. Composition: 33 ohms ±10%, 1/2 w.				C6		(Part of T1).	C410			L428 and	7488079P18	Choke, RF: 15 μh $\pm 10\%$, 1.2 ohms DC res; sim to Jeffers 4421-9K.	L450			
		JACKS AND RECEPTACLES	R36	3R77P681J	Composition: 680 ohms ±5%, 1/2 w.				C7		(Part of T2).	and C411		Refer to mechanical Parts (RC-1025).	L429		to seriers 4721-5K.			MECHANICAL PARTS	
J1	4033513P4	Contact, electrical; sim to Bead Chain L93-3.	R38	3R77P081J 3R77P752J	Composition: 7500 ohms ±5%, 1/2 w.	RT1	5490828P41	Thermistor: 30 ohms ±10%, color code black, white; sim to Globar Type Bl2llH-4.	C8	5496219P238	Ceramic disc: 7 pf ±5%, 500 VDCW; temp coef -80 PPM.	C411	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW;	L430 and	7488079P6	Choke, RF: 1.0 µh ±10%, 0.30 ohms DC res; sim to Jeffers 4411-8K.			(SEE RC-1823)	
thru J22			R39	3R77P820J	Composition: 8200 ohms ±5%, 1/2 w.	RT2	5490828P9	Thermistor: 10,000 ohms ±10%, color code	с9	5490008P135	Silver mica: 220 pf ±10%, 500 VDCW; sim to	and C413	3453352F1	sim to Allen-Bradley Type FASC.	L431		to verters that our	1	19c303396G4	Bottom cover. (Station)	. I6 " <u>^</u> "
İ	<u> </u>	INDUCTORS	R40*	3R77P221J	Composition: 220 ohms ±5%, 1/2 w.	and RT3		yellow; sim to Ġlobar Type 55ĺH-8.	c10	5494481P112	Electro Motive Type DM-15. Ceramic disc: .001 pf ±10%, 500 VDCW; sim	C414		Refer to Mechanical Parts (RC-1823).	L432	19A127433P1	Coil.		19C3O3385G1	Bottom cover. (Mobile)	. ^
L1	19A115711P6	Transformer, freq: 455 KHz; sim to TOKO PEFCN-		0	In REV G and earlier:				thru	5494481P112	to RMC Type JF Discap.	thru C418			L433 and	19A115700P2	Bead, ferrite.	2	19C317344P3	Heat sink.	.
		14733-CX12.		3R77P241J	Composition: 240 ohms ±5%, 1/2 w.	Tl	19A116040P1	Audio freq: 300 to 4000 Hz, Pri: 19.3 ohms ±10% DC res.	C14		DIODES AND RECTIFIERS	C419	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW;	L434			3	19A121723P1	Support. (Mounts C425 and C426)	
1.2	19A115711P7	Transformer, freq: 455 KHz; sim to TOKO PEFCN-14734-BNL2.	R41	3R152P240J	Composition: 24 ohms ±5%, 1/4 w.			Sec: 23.5 ohms ±10% DC res.	CR1	19A115250Pl	Silicon.	thru C422		sim to Allen-Bradley Type FA5C.				4	4033089Pl	Clip. (Part of XY1-XY4).	,
L3	19A127134G1	Choke.	R42	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.	A430		HIGH IF AMPLIFIER	thru CR5	15811020071		C423		Refer to Mechanical Parts (RC-1598).	P305 thru P311	4029840P2	Contact, electrical: sim to Amp 42827-2.	5	19B200525P9	Rivet. (Part of XYl-XY4).	
1			R43	19B209358P101	Variable, carbon film: approx 25 to 250 ohms	A TOO		19B216356G2	Cas		JACKS AND RECEPTACLES	and C424						6	19A115793P1	Contact. (Part of XY1-XY4).	17 18 19
01	19A115123P1	Silicon, NPN,			$\pm 10\%$, 0.2 w; sim to CTS Type X-201.			CAPACITORS		4033513P4	Contact, electrical: sim to Bead Chain L93-3.	C425	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW;	P312	4029840P3	Contact, electrical: sim to Amp 42101-2.	7	4039307P1	Crystal socket. (Part of XY1-XY4).	.
thru	19411312321	Silicon, NPN.	R44	19B209022P101	Wirewound: 0.27 ohms ±10%, 2 w; sim to IRC Type BWH.	C1	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	thru J6	10000101		thru C427		sim to Allen-Bradley Type FA5C.	P313 thru	4029840P2	Contact, electrical: sim to Amp 42827-2.	8	4035306P40	Fiber washer. (Used with Y2 on A425).	
05	19A115889P1	Silicon, NPN.	R46	3R77P913J	Composition: 91,000 ohms ±5%, 1/2 w.			RMC Type JF Discap.	J15	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	C428	5496267P11	Tantalum: 68 µf ±20%, 15 VDCW; sim to	P322			9	4034252P5	Can. (Used with Tl on A425).	
06	19A115123P1	Silicon, NPN.	R47	3R152273K	Composition: 27,000 ohms ±10%, 1/4 w.	C2*	7489162P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	and J16		,			Sprague Type 150D.	P323	4029840P1	Contact, electrical: sim to Amp 41854.	10	19C3O3389G1	Chassis.	, -
07*	19A115300P4	Silicon, NPN.	R49	3R77P103J	Composition: $10,000$ ohms $\pm 5\%$, $1/2$ w.			In 19E500881G5 REV H and earlier:				C429	19A115680P4	Electrolytic: 50 μf +150% -10%, 25 VDCW; sim to Mallory Type TT.	P324	4029840P2	Contact, electrical: sim to Amp 42827-2.	11	19A121722P1	Plate.	, -
08	19A115123P1	Silicon, NPN.	R50	3R77P222J	Composition: 2200 ohms ±5%, 1/2 w.		1	In 19E500881G6 REV J and earlier: In 19E500881G7 REV H and earlier:	Lı	7488079P16	Choke, RF: 10 µh ±10%, 0.6 ohm DC res max;	C430	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW;	P325	4029840P1	Contact, electrical: sim to Amp 41854.	12	4036765G4	Screw. (Part of C410, C411, C414-C418, C423 and C424).	,
, m	19A115362P1	Silicon, NPN: sim to Type 2N2925.	R51	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.			In 19E500881G8 REV J and earlier:	and L2		sim to Jeffers 4421-7K.	and C431		sim to Allen-Bradley Type FA5C.	P326	4029840P2	Contact, electrical: sim to Amp 42827-2.	1,,	7117825P1	Washer. (Part of C410, C411, C414-C418, C423	
910*	19A116774P1	Silicon, NPN: sim to Type 2N5210.	R52	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.		5490008P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	L5	-	(Part of Tl and T2).	C433	5493392P107	Ceramic, stand-off: 1000 pf +100%-0%, 500 VDCW;	P327	4029840P1	Contact, electrical: sim to Amp 41854.	13	7117623F1	and C424).	.
1	15,111,111	In REV F and earlier:	R55	3R77P103K	Composition: 10,000 ohms $\pm 10\%$, 1/2 w.	С3	5496218P650	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef	L6	7488079P35	Choke, RF: 2.20 µh ±10%, 0.50 ohms DC res max;			sim to Allen-Bradley Type SS5D.	P328 thru	4029840P2	Contact, electrical: sim to Amp 42827-2.	14	19A121724P1	Support. (Mounts C419 and C420).	.
	19A115123P1	Silicon, NPN.	R56	3R77P224J	Composition: 0.22 megohm ±5%, 1/2 w.			-150 PPM.			sim to Jeffers 4412-9K.	C435 and	7774750P4	Ceramic disc: .001 µf +100% -0%, 500 VDCW.	P335			15	19A127372Pl	Support. (Mounts C427, C430 and C431).	,
	10	January Marie	R57	3R77P103K	Composition: 10,000 ohms $\pm 10\%$, 1/2 w.	C4	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	1		TRANSISTORS	C436			P410 and	4029840P2	Contact, electrical: sim to Amp 42827-2.	16	7145451P1	Cable clamp.	,
		RESISTORS	R58	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.	C5	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.	Q1 *	19A115440P1	Silicon, NPN.	C437	5493392P3	Ceramic, feed-thru: 47 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.	P411			17	19B204583G3	Hinge.	1
R1	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	R59	3R77P393K	Composition: 39,000 ohms ±10%, 1/2 w.	and C6			,		In REV A and earlier:	C438	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.			TRANSISTORS	18	19B216727P1	Support. (Used with Q410 and Q411).	1
R2	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.	R60	3R77P103K	Composition: 10,000 ohms $\pm 10\%$, 1/2 w.			TRANSISTORS		19A115330Pl	Silicon, NPN.	C439	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	Q410* and	19A116741P2	Silicon, NPN.	19	19A116023P2	Plate, insulated. (Used with Q410 and Q411).	4
R3	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.	and R61		·	Q1*	19A115440P1	Silicon, NPN.	1	•		and C440		RMC Type JF Discap.	Q411*		In 19E500881G5 REV J and earlier: In 19E500881G6 REV K and earlier: In 19E500881G7 REV J and earlier:	20	19A116022P1	Insulator, bushing. (Used with Q410 and Q411).	1
R4	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.	R62*	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w. Deleted		İ	In 19E500881G5 REV K and earlier:			RESISTORS	C441*	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW;			In 19E500881G7 REV J and earlier: In 19E500881G8 REV K and earlier:	21	4029851P6	Clip, loop.	4
R5	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	R64*	3R77P120J	by REV C. Composition: 12 ohms ±5%, 1/2 w.	1		In 19E500881G6 REV L and earlier: In 19E500881G7 REV K and earlier:	Rl	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	11		sim to Allen-Bradley Type FA5C. Added by REV F.		19A116203P2	Silicon, NPN.	22	19B204583G1	Hinge.	1
R6	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.	K04*	387791203	In REV B and earlier:			In 19E500881G8 REV L and earlier:	R2	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.			DIODES AND RECTIFIERS				23	19B204583G2	Hinge.	1
R7	3R77P823K	Composition: 82,000 ohms $\pm 10\%$, $1/2$ w.		3R77P180J	Composition: 18 ohms ±5%, 1/2 w.		19A115328P1	Silicon, NPN.	R3	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	CR1	19A116062P2	Selenium.	R410	19A116278P444	Metal film: 0.28 megohm ±2%, 1/2 w.	24	19A121676P1	Guide pin.	1
R8	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.	R66	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.			RESISTORS	R4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.			JACKS AND RECEPTACLES	R410	3R78P390K	Composition: 39 ohms ±10%. 1 w. Added by REV B.	25	19C3O3495G3	Top cover. (Station, except Repeaters and VM).	1
R9	3R77P102K	Composition: 1000 ohms $\pm 10\%$, $1/2$ w.	R67	3R152P273K	Composition: 27,000 ohms ±10%, 1/2 w.	R1	3R152P301J	Composition: 300 ohms ±5%, 1/4 w.	R5 and	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	J441		(Part of W441).	R411*	3R76P39UR	Composition. 39 onns 210%, 1 w. Added by REV B.		19C3O3676G2	Top cover. (Station, Repeater and VM only).	1
R10	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.	R68	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.	R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	R6	0-5500504	Composition: 2700 ohms ±10%, 1/2 w.	J442	19B205689G2	Connector: 18 contacts rated at 5 amps min					19C3O3385P2	Top cover. (Mobile).	(
R11	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.	R69	3R77P752J	Composition: 7500 ohms ±5%, 1/2 w.	R3*	3R152P152J	Composition: 1500 ohms ±5%, 1/4 w.	R7	3R77P272K	Composition: 2700 onms 110%, 1/2 w.	1 3442	19820308902	at 1000 VDC max.	Т410	19A116041P2	Audio freq: 300 Hz to 4000 Hz, Pri: 1.00 ohm ±15% DC res.	26	19A121297P2	Angle.	(
R12	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.	R71	3R77P133J	Composition: 13,000 ohms ±5%, 1/2 w.			In 19E500881G5 REV K and earlier:		1		J443	19C3O3426G1	Connector: 20 pin contacts.			Sec 1: 0.23 ohm ±10% DC res, Sec 2: 10.5 ohms ±15% DC res.	27	7160861P4	Nut, sheet spring. (Used to secure cover).	
R13	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.	R72	3R77P362J	Composition: 3600 ohms ±5%, 1/2 w.			In 19E500881G6 REV L and earlier: In 19E500881G7 REV K and earlier: In 19E500881G8 REV L and earlier:	T1 and		COIL ASSEMBLY Tl 19B204950G1	J444		(Part of W444).			1	28	4036555Pl	Insulator, disc. (Used with Q7 on A427).	(
R14	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.	R73	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.		3R152P302J	Composition: 3,000 ohms ±5%, 1/4 w.	T2		T2 19B204950G2			INDUCTORS		1	TERMINAL BOARDS	29	4035267P2	Button, plug.	(
R15	3R77P333J	Composition: 33,000 ohms ±5%, 1/2 w.	R74	3R77P362J	Composition: 3600 ohms ±5%, 1/2 w.		3R152P682J	Composition: 6800 ohms ±5%, 1/4 w.				L410 .	19B204938G8	Coil,	TB1	7487424P2	Miniature, phen: 1 terminal.				1
R16	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.	R75*	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w. Deleted	P5	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	r6	5496218P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef	L411	19B204938G15	Coil.	TB2	7487424P26	Miniature, phen: 6 terminals.				1
	3R152P471J	Composition: 470 ohms ±5%, 1/4 w.			by REV C.	P7	3R152P101R	Composition: 510 ohms ±5%, 1/4 w.		34302101203	-80 PPM.	L412	19B204938G8	Coil.	тв3	7487424P24	Miniature, phen: 3 terminals.				1
R20 R23	3R152P472K 3R77P104K	Composition: 0.10 percent +10% 1/2 w	R76*	3R152P912J	Composition: 9100 ohms ±5%, 1/4 w. Deleted by REV C.	"	0		C7	5496218P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -80 PPM.	L413	19B204938G16	Coil.							1
R23	3R77P104K 3R152P102J	Composition: 0.10 megohm ±10%, 1/2 w. Composition: 1000 ohms ±5%, 1/4 w.	R77*	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.			TRANSFORMERS				L414	19B204938G11	Coil.	W441	19B205634G3	Coaxial cable: 50 ohm, approx 5 inches long.				(
R24	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	l		In REV B and earlier:	T1	19B216372G1	Coil, includes tuning slug 5491798P7.				L415	19B204936P13	Coil.			Includes (J441) 19B209122P3 connector.				1
and	JRITTIOSK	Composition. 10,000 omms 210k, 1/2 w.		3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	A432		OSCILLATOR/MULTIPLIER BOARD	L5	19A121728P1	Coil.	thru L417			W444	19B205634G7	Coaxial cable: 50 ohm, approx 7 inches long. Includes (J444) 19B209122P4 connector.				1
R27	3R77P753J	Composition: 75,000 ohms ±5%, 1/2 w.	R78*	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.	thru A435		A432 19c311726G1 A433 19c311726G2		5491798P7	Tuning slug.	L418	19B204938G17	Coil.	W445	19A122550G1	RF: 50 ohm imp, approx 4 inches long.				1
and R28		50mposteron. 10,000 0mm 20%, 1/2 m			In REV C and earlier:		1	A434 19c311726G3 A435 19c311726G4		1	SOCKETS	L419	19B204938G12	Coil.							1
R29	3R77P182J	Composition: 1800 ohms ±5%, 1/2 w.		3R77P100J	Composition: 10 ohms $\pm 5\%$, $1/2$ w.				XY1	19B216043G1	Socket.	L420	19B204936P14	Coil.			MULTI-FREQUENCY MODIFICATION KIT 19A127096-Gl and G2				1
R30*	3R77P821J	Composition: 820 ohms ±5%, 1/2 w.	R79	3R152P393J	Composition: 39,000 ohms $\pm 5\%$, $1/4$ w.		1	CAPACITORS	thru XY4			thru L422									(
		In REV C and earlier:	R80*	3R152P272J	Composition: 2700 ohms $\pm 5\%$, $1/4$ w.	C1 thru	5494481P112	Ceramic disc: 1000 pf ±10%, 500 VDCW; sim to RMC Type JF Discap.		1		L423	19B204938G18	Coil.		19A127136G1	Harness assembly.				(
	3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.			In REV C-K:	C3	1				NOTE: When reordering specify ICOM Frequency.	L424	19B204938G19	Coil.	P301 thru	4029840P2	Contact, electrical; sim to Amp 42827-2. (Part of 19A127136Gl Harness assembly).				1
				3R152P432J	Composition: 4300 ohms $\pm 5\%$, $1/4$ w. Added by				1	1	ICOM Freq = Operating Freq -12.4 MHz - 24.	11			P304						1
1					REV C.				Yl thru	4EG26A10	Integrated Circuit Oscellator Module (ICOM).										(
]						1		Y4												1
										19D413070P1	Cap, decorative.										1
																1					(
	[l L				1		J L	1			1			_1		



PRODUCTION CHANGES

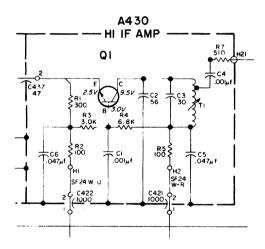
Changes in the equipment to improve performance or to simplify carcuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. B Chassis and RF Circuit 19E500881G5 thru G8
- REV. A 2nd Mixer Board A425, 19B216119G2
- REV. B IF Audio and Squelch Board A427, 19D413129G2

INCORPORATED INTO INITIAL SHIPMENT.

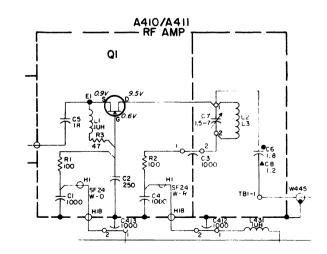
- Chassis and RF Circuit 19E500881G5 thru G8
- REV. C To incorporate a new multiplier transistor and decouple the supply voltage. Changed Q1. Added C15 and R7.
- REV. D To eliminate squelch opening thump. Removed the white/ orange wire between J443-13 and TB2-1. Added a whilte/ orange wire between P312 (or J17 on IF Audio and squelch board) and TB2-1.
- REV. E To improve stability of the multiplier boards A413 and A414. Deleted C9.
- REV. F To improve sensitivity. Added C411 to Hi IF Amplifier A430.

Schematic Diagram was:



REV. G - To stabilize the R.F. Amplifier and to improve the band-end tuning of the multiplier assembly. Changed the RF amplifier board. Changed C5, C7 and C8 on the Multiplier Assembly.

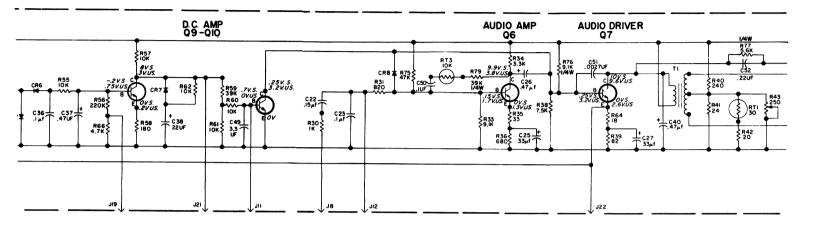
Schematic Diagram was:



IF Audio and Squelch Board A427, 19D413129G2

REV. C - To eliminate barely audible squelch switching transients and to reduce receiver squelch tail. Deleted C38, C49, CR7, CR8, R62, R75 and R76. Added C55, R80, R81 and R82. Changed C27, C36, R53, R64 and R77.

Schematic Diagram was:



REV. D - To improve frequency response. Changed R30 and R78.

REV. E - To compensate for vendor change. Changed C26.

REV. D - To improve frequency response. Changed R30 and R78.

REV. E - To compensate for vendor change. Changed C26.

REV. F - To incorporate silicon diodes. Changed CR3 & CR4.

REV. H - To improve PA bias. Changed R40.

REV. J - To improve stability of audio output with no load. Added R85.

REV. K - To improve frequency response. Deleted R85 and changed C40 $_{\bullet}\,$

REV. L - To reduce audio distortion. Changed R80.

REV. N - To improve stability. Changed Q5.

Chassis and RF Circuit 19E500881G5, G7

REV. H - To improve operation. Deleted CR1.

REV. J - To improve operation of mixer (A412). Changed C2 and added C8.

REV. K - To incorporate new transistors. Changed Q410, Q411.

REV. L - To improve intermodulation performance.
Changed R3 and Q1.

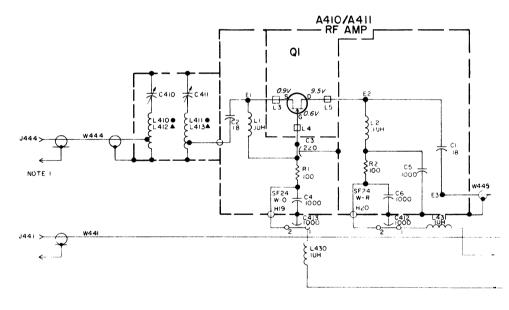
REV. M - To improve sensitivity. Changed C3.

REV. M - Chassis and RF Circuit 19E500881G Chassis and RF Circuit 19E500881G

To incorporate a new RF Amplifier Assembly. Changed A410/A411.

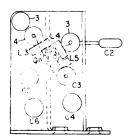
Schematic Diagram Was:

REV. G - To ensure squelch action at -30°C. Changed Q10. Chassis and RF Circuit 19E500881G6 and G8 REV. H - To improve band-end tuning in multiplier board A413/A414. Changed C6 and C8. REV. J - To improve operation. Deleted CR1 REV. K - To improve operation of Mixer (A412) Changed C2 and added C8. REV. L - To incorporate new transistors. Changed Q410 and Q411. REV. M - To improve frequency response. Changed C26. REV. M - To improve intermodulation performance. Changed R3 and Q1. To improve sensitivity. Changed C3. OSCILLATOR/MULTIPLIER BOARD A432 THRU A435 19C311726G1-G4 REV. B - To incorporate a new transistor. Changed Q1. Chassis and RF Circuit 19E500881G5



Outline Diagram Was:

RF AMP A410/A411



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ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- 1. GE Part Number for component
- 2. Description of part
- 3. Model number of equipment
- 4. Revision letter stamped on unit

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY ● LYNCHBURG, VIRGINIA 24502

